

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_{D \text{ max}}$ $T_A = +25^\circ\text{C}$
30V	10m Ω @ $V_{GS} = 10\text{V}$	12.0A
	16m Ω @ $V_{GS} = 4.5\text{V}$	10.4A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions

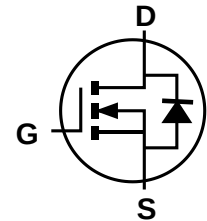
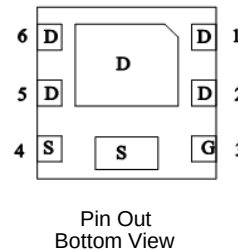
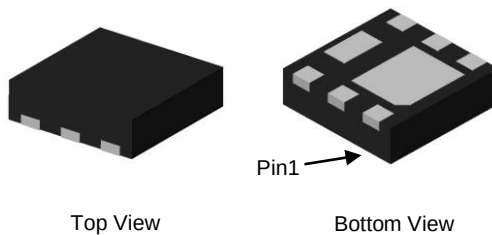
Features

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208④
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6



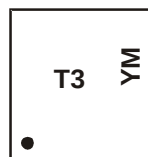
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Quantity per reel
DMT3008LFDF-7	T3	7	3,000
DMT3008LFDF-13	T3	13	10,000

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

U-DFN2020-6



T3 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021
Code	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10.0V	Steady State	T _A = +25°C T _A = +70°C	I _D	12.0 9.5	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	13.6 11.0	A
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	10.4 8.4	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	11.9 9.6	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	70	A
Maximum Body Diode Continuous Current			I _S	2	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	8	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	3.2	mJ

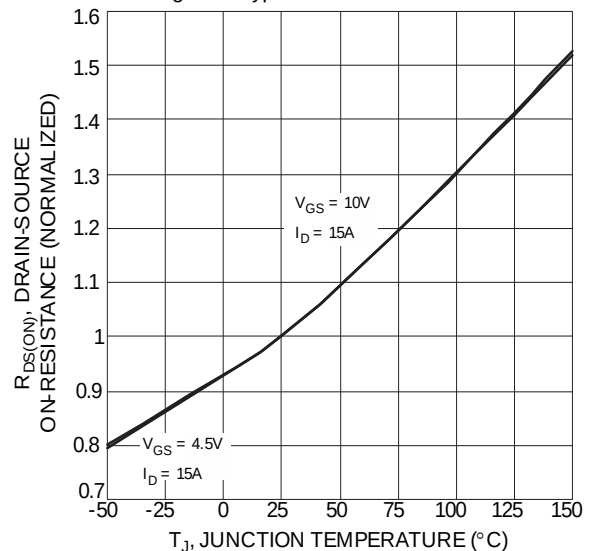
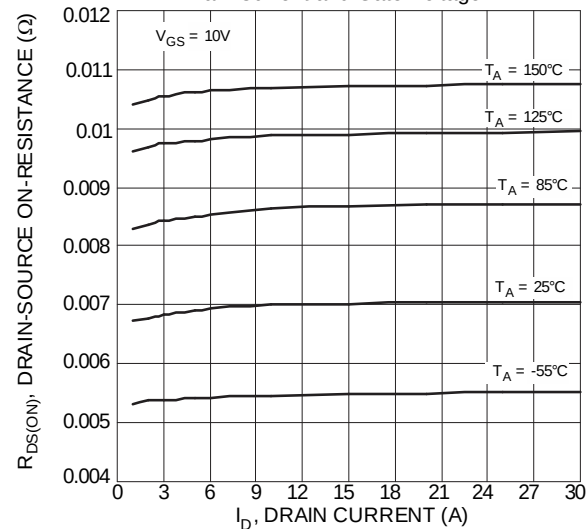
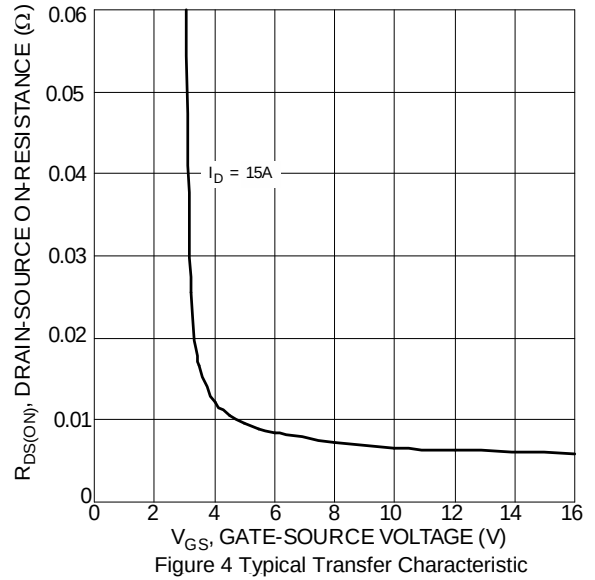
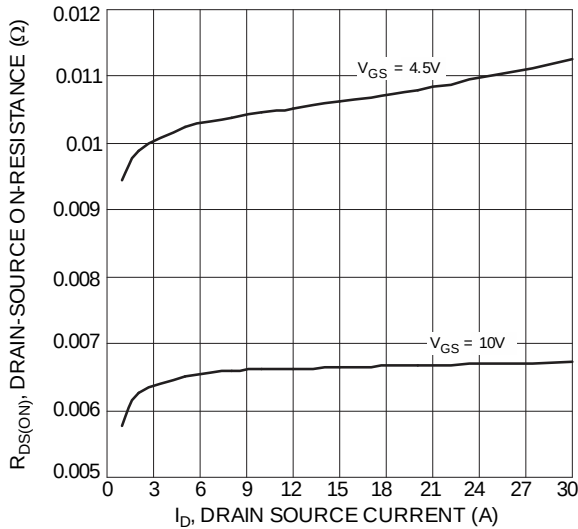
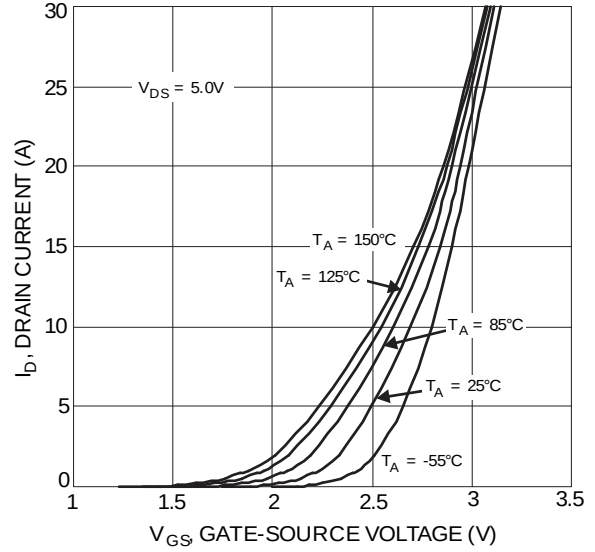
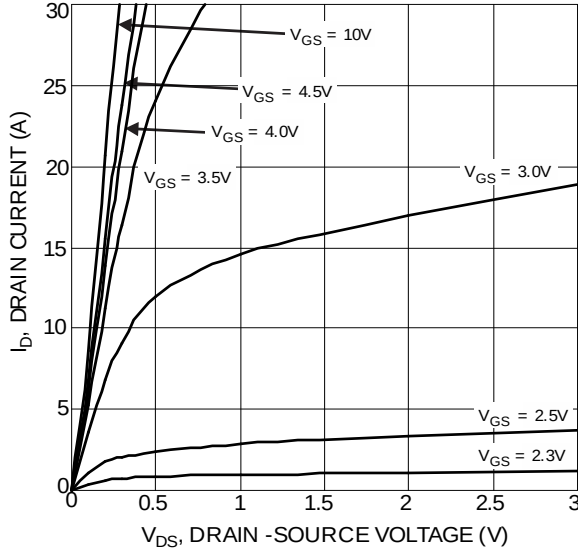
Thermal Characteristics

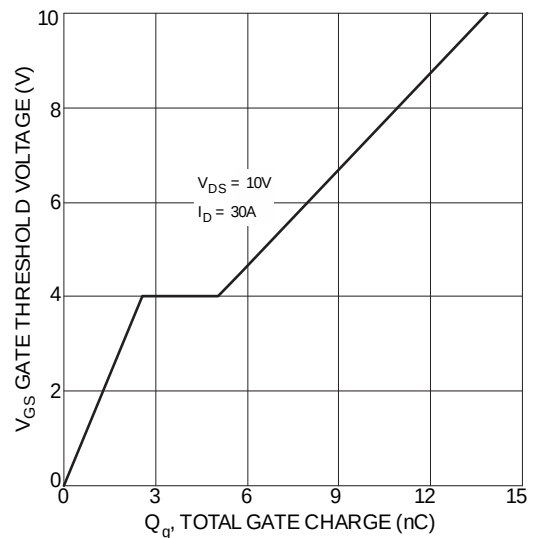
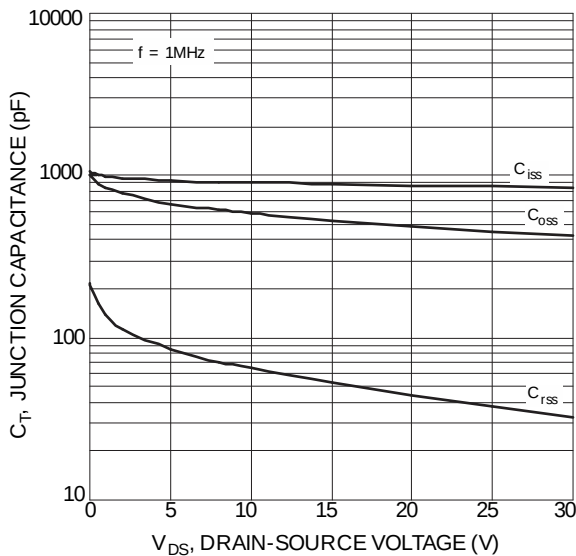
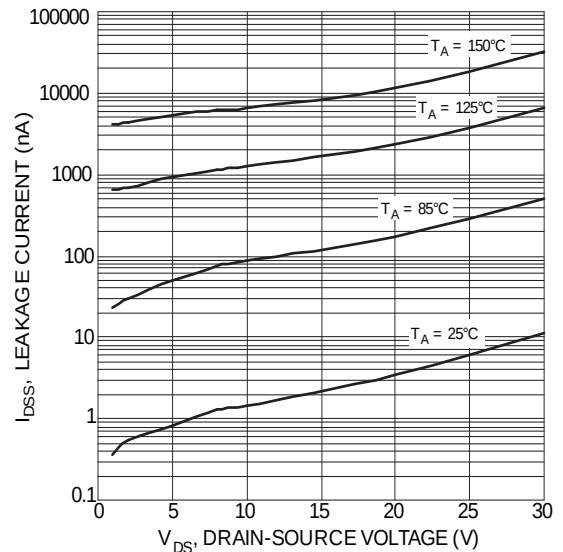
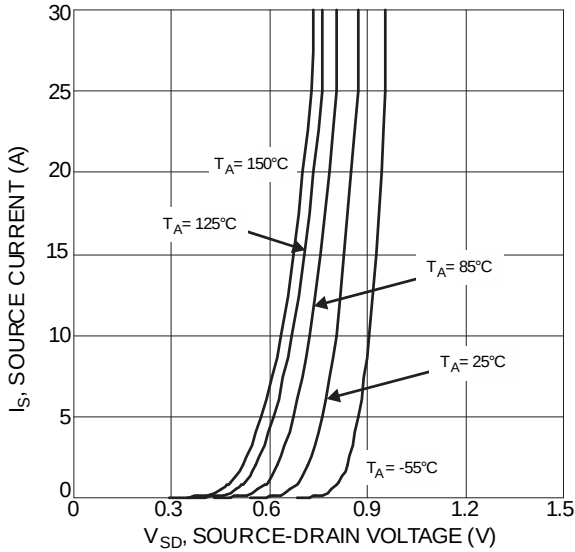
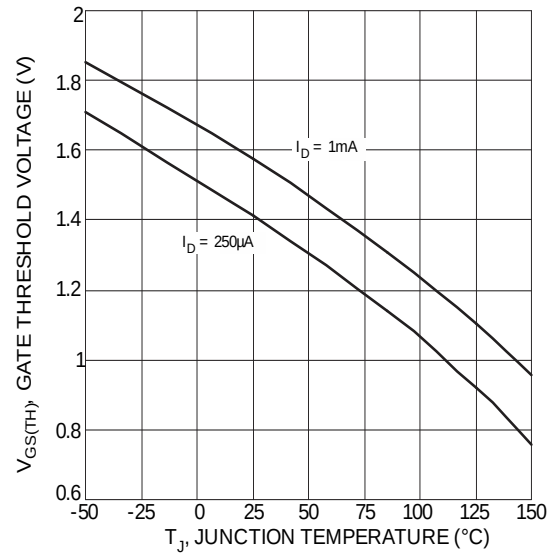
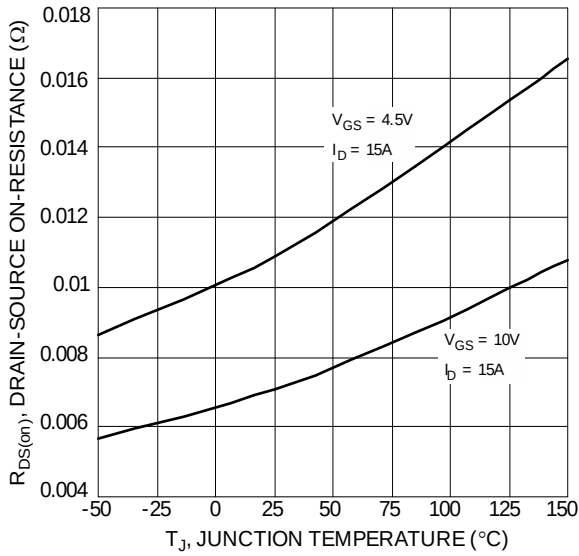
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.8	W
	T _A = +70°C		0.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	156	°C/W
	t < 10s		116	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.1	W
	T _A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	60.8	°C/W
	t < 10s		45.0	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	13	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

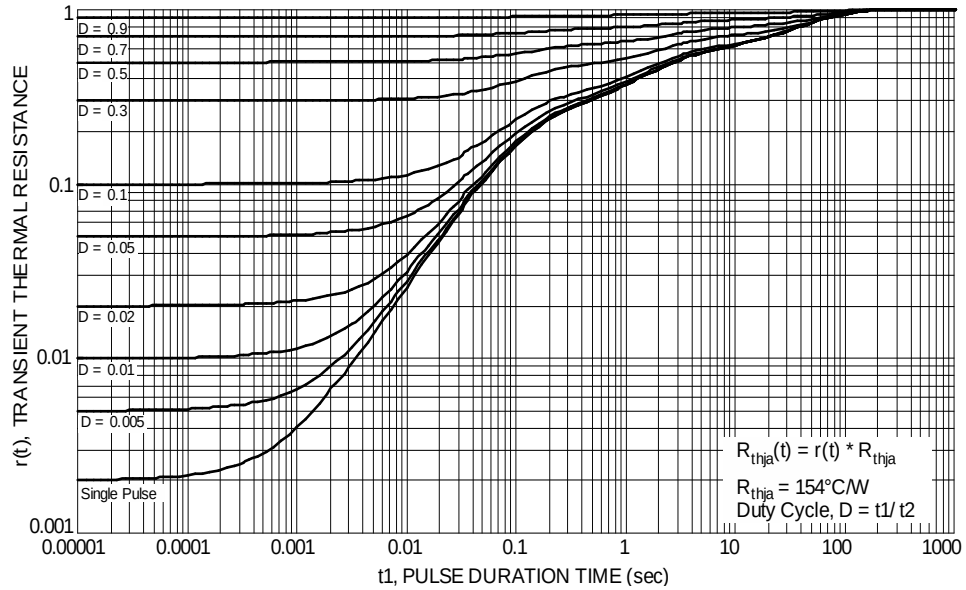
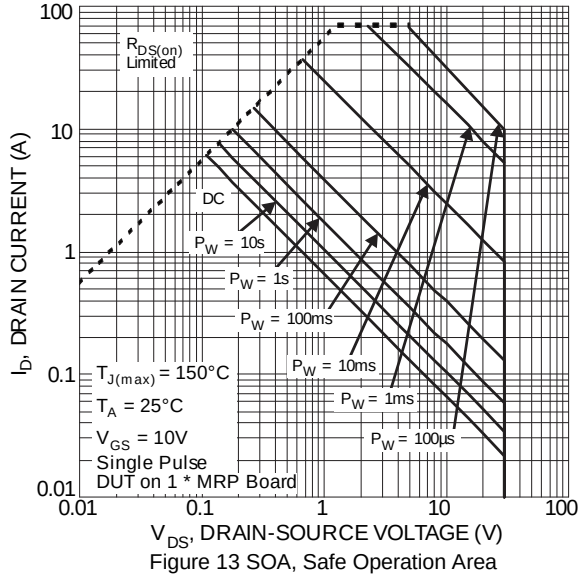
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30.0	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	10.0	mΩ	V _{GS} = 10V, I _D = 9.0A
			—	16.0		V _{GS} = 4.5V, I _D = 8.5A
Diode Forward Voltage	V _{SD}	—	—	1.2	V	V _{GS} = 0V, I _S = 2A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	886	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	531	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	53	—	pF	
Gate Resistance	R _g	—	1.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	14	—	nC	V _{DD} = 10V, I _D = 30A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	5.8	—	nC	
Gate-Source Charge	Q _{gs}	—	2.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.8	—	ns	V _{DD} = 10V, V _{GS} = 10V, R _L = 0.67Ω, R _G = 4.7Ω, I _D = 15A
Turn-On Rise Time	t _R	—	1.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	12.5	—	ns	
Turn-Off Fall Time	t _F	—	3.6	—	ns	
Reverse Recovery Time	t _{RR}	—	18.4	—	ns	I _F = 15A, dI/dt = 100A/μs
Reverse Recovery Charge	Q _{rr}	—	7.6	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.



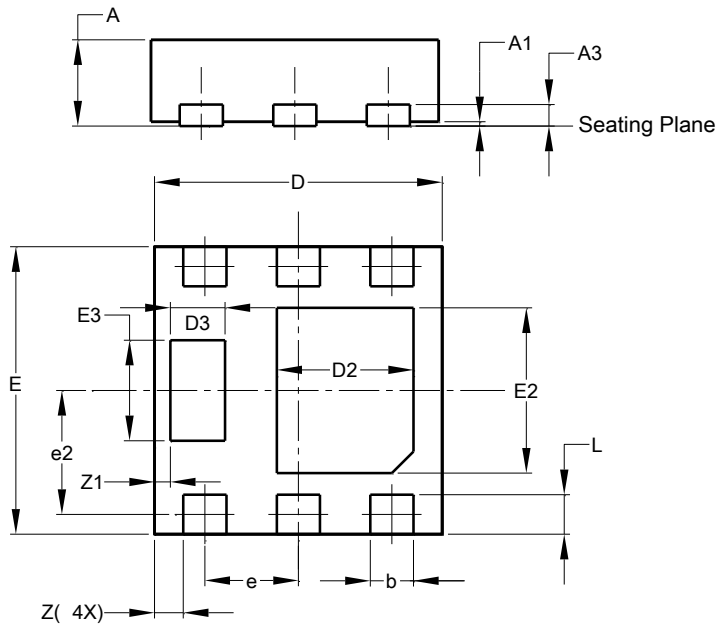




Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

(1) Package Type: U-DFN2020-6 (Type F)

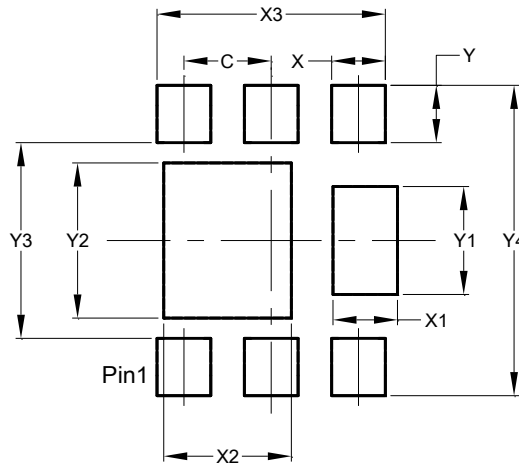


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D3	0.33	0.43	0.38
e	0.65 BSC		
e2	0.863 BSC		
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E3	0.65	0.75	0.70
L	0.225	0.325	0.275
Z	0.20 BSC		
Z1	0.110 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

(1) Package Type: U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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